

**In the Claims**

Please amend the claims as follows:

Claims 1-43 (Cancelled)

44. (Currently Amended) A method of manufacturing an epitaxial silicon wafer substrate comprising:

Setting an upper limit that is defined by a straight line connecting a point at which a nitrogen concentration in a silicon ingot is  $3 \times 10^{15}$  atoms/cm<sup>3</sup> when an oxygen concentration in the silicon ingot is  $7 \times 10^{17}$  atoms/cm<sup>3</sup> and a point at which the nitrogen concentration is  $3 \times 10^{14}$  atoms/cm<sup>3</sup> when the oxygen concentration is  $1.6 \times 10^{18}$  atoms/cm<sup>3</sup> within a concentration range where the oxygen concentration and the nitrogen concentration are plotted along the horizontal axis and the vertical axis, and also setting a lower limit of the amount of added nitrogen, which is a function of an initial oxygen concentration of a silicon wafer substrate for ensuring a sufficient density of oxygen precipitates as gettering sites;

controlling ~~an~~ the oxygen concentration in accordance with a change in a the nitrogen concentration based on a characteristic that the nitrogen concentration increases from a shoulder portion to a tail portion of ~~a the~~ silicon ingot, so that the oxygen concentration and the nitrogen concentration fall within ~~a the upper limit and the lower limit concentration range where an upper limit is defined by a line connecting a point at which the nitrogen concentration is  $3 \times 10^{15}$  atoms/cm<sup>3</sup> when the oxygen concentration is  $7 \times 10^{17}$  atoms/cm<sup>3</sup> and a point at which the nitrogen concentration is  $3 \times 10^{14}$  atoms/cm<sup>3</sup> when the oxygen concentration is  $1.6 \times 10^{18}$  atoms/cm<sup>3</sup> within the concentration range where the oxygen~~

~~concentration and the nitrogen concentration are plotted along the horizontal axis and the vertical axis~~ at the same time when the silicon ingot is pulled up from a silicon raw material melt doped with nitrogen so that the nitrogen concentration at the tail portion of the silicon ingot is less than  $3 \times 10^{15}$  atoms/cm<sup>3</sup>;

Obtaining the silicon wafer substrate by slicing the pulled-up silicon ingot; and mirror polishing the obtained silicon wafer substrate; and then immediately after the step of mirror polishing, subjecting the obtained silicon wafer substrate to epitaxial growth processing.